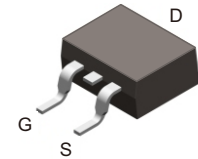


## ACMS100N04D2-HF

**N-Channel  
RoHS Device  
Halogen Free**

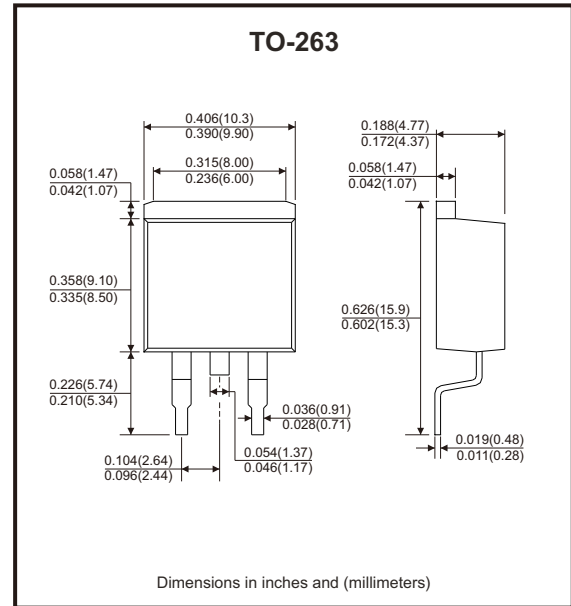


### Features

- Super low  $R_{DS(on)}$  and gate charge.
- Advanced shielded-gate technology.
- Green device available.
- AEC-Q101 Qualified.

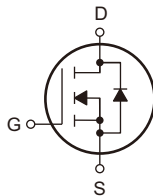
### Mechanical data

- Case: TO-263, molded plastic.
- Molding compound: UL flammability classification rating 94V-0.
- Terminals: Matte tin-plated leads, solderability per MIL-STD-202, method 208.



### Circuit Diagram

- G : Gate
- S : Source
- D : Drain



### Maximum Ratings (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DSS}$	40	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	V
Continuous drain current (package limit) $T_c=25^\circ\text{C}$ (Note 1)	$I_D$	100	A
Continuous drain current (silicon limit) $T_c=25^\circ\text{C}$ (Note 1)	$I_D$	220	
Continuous drain current (silicon limit) $T_c=100^\circ\text{C}$ (Note 1)	$I_D$	140	
Pulsed drain current ( $t_p < 10\mu\text{s}$ )	$I_{DM}$	880	A
Single pulse avalanche energy (Note 3)	$E_{AS}$	65	mJ
Power dissipation ( $T_c=25^\circ\text{C}$ )	$P_D$	156	W
Thermal resistance junction to case (Note 1)	$R_{\theta JC}$	0.8	$^\circ\text{C/W}$
Thermal resistance junction to air	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Operating junction temperature range	$T_J$	-55 to +150	$^\circ\text{C}$
Storage temperature range	$T_{STG}$	-55 to +150	$^\circ\text{C}$

## Electrical Characteristics (at T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	40			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
<b>On Characteristics</b>						
Static drain-source on-resistance (Note 2)	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A		1.7	2	mΩ
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A		2.0	2.4	mΩ
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1	1.5	2.5	V
<b>Dynamic Characteristics</b>						
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V, f = 150kHz		6269		pF
Output capacitance	C <sub>oss</sub>			2818		
Reverse transfer capacitance	C <sub>rss</sub>			222		
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> = 20V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 100A		112		nC
Gate to source charge	Q <sub>gs</sub>			21		
Gate to drain (miller) charge	Q <sub>gd</sub>			14.6		
<b>Switching Characteristics</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20V, V <sub>GS</sub> = 4.5V R <sub>G</sub> = 3Ω, I <sub>D</sub> = 20A		24		ns
Turn-on rise time	t <sub>r</sub>			84		
Turn-off delay time	t <sub>d(off)</sub>			62		
Turn-off fall time	t <sub>f</sub>			20		
<b>Source-Drain Diode Characteristics</b>						
Diode forward voltage (Note 2)	V <sub>SD</sub>	I <sub>SD</sub> = 50A, V <sub>GS</sub> = 0V			1.2	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 20A, V <sub>R</sub> = 30V, di/dt = 100A/μs		152		ns
Reverse recovery charge	Q <sub>rr</sub>				375	

- Notes: 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.  
 2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%.  
 3. The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=30V, V<sub>GS</sub>=10V, L=0.1mH.  
 4. The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

## Rating and Characteristic Curves (ACMS100N04D2-HF)

Fig.1 - Output Characteristics

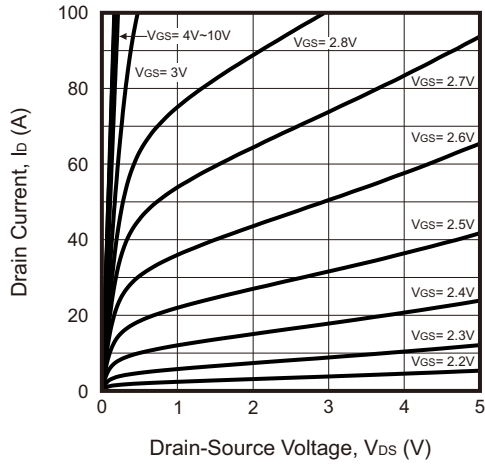


Fig.2 - On-Resistance vs. Drain Current and Gate Voltage

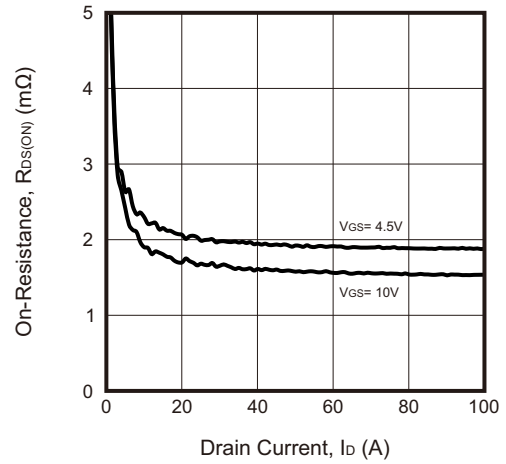


Fig.3 - On-Resistance vs. Gate-Source Voltage

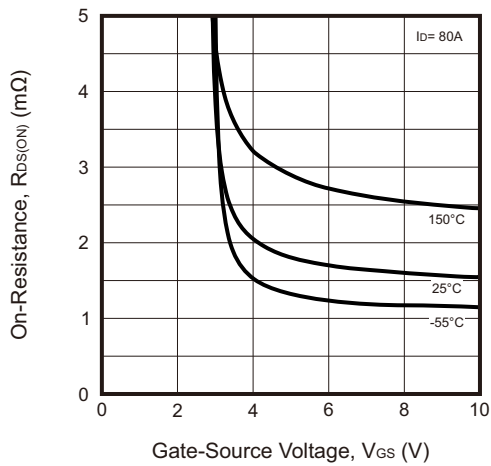


Fig.4 - Body-Diode Characteristics

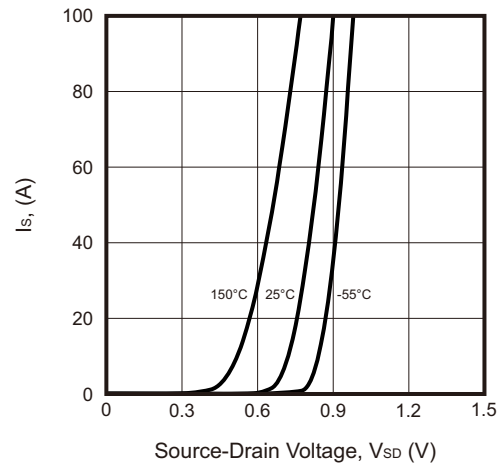


Fig.5 - On-Resistance vs. Junction Temperature

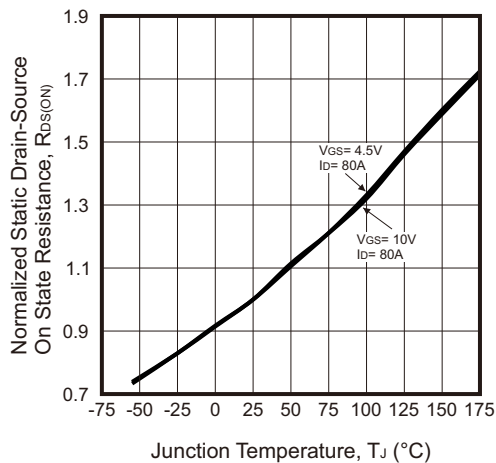
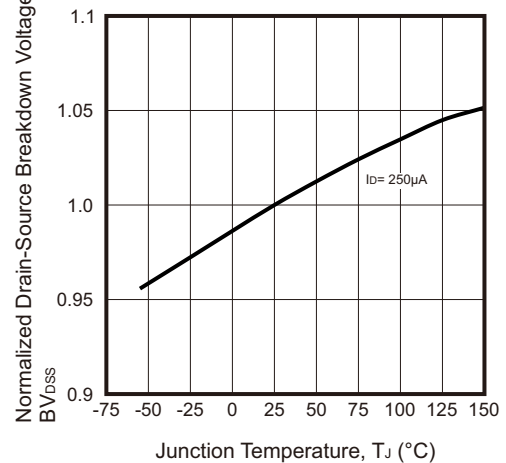


Fig.6 - Drain Source vs. Junction Temperature



## Rating and Characteristic Curves (ACMS100N04D2-HF)

Fig.7 - Capacitance Characteristics

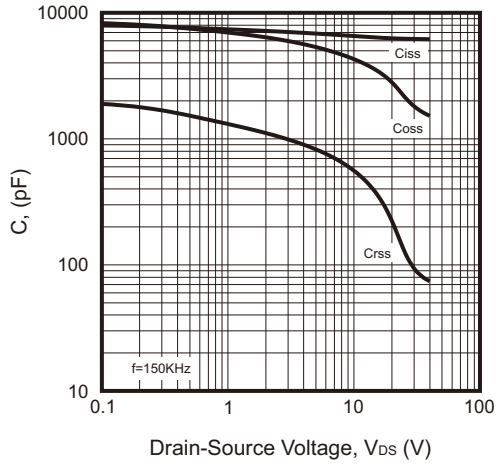


Fig.8 - Gate Voltage vs. Junction Temperature

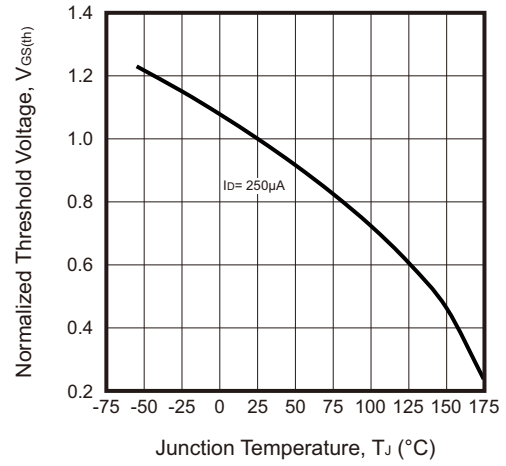


Fig.9 - Transfer Characteristics

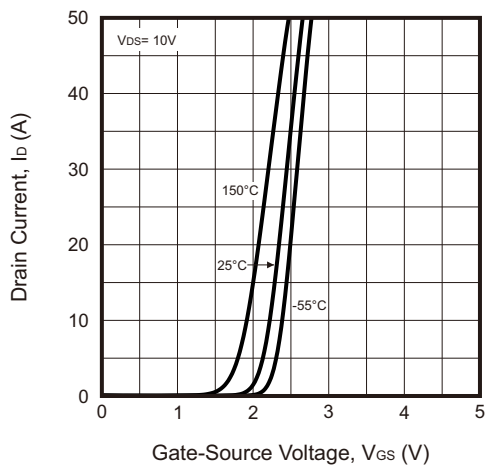
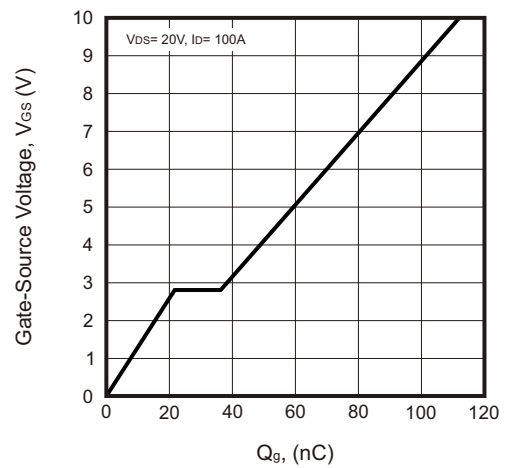
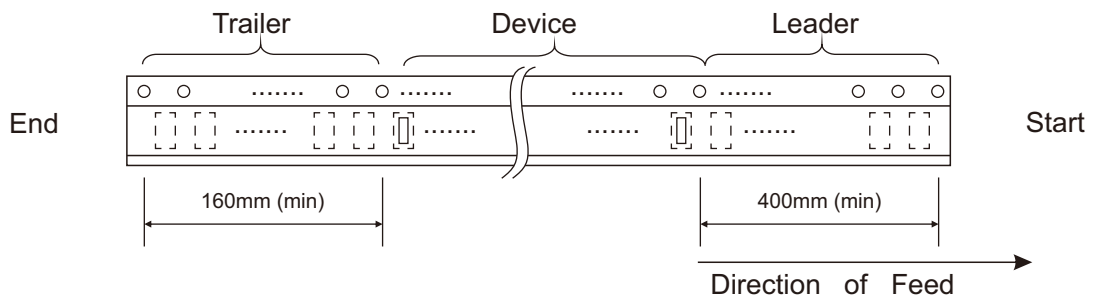
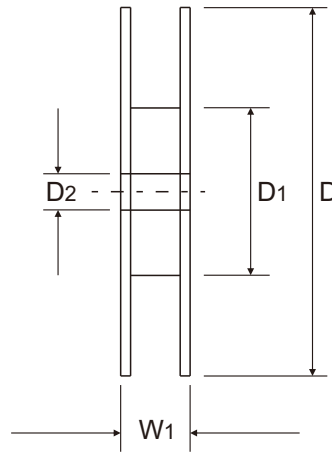
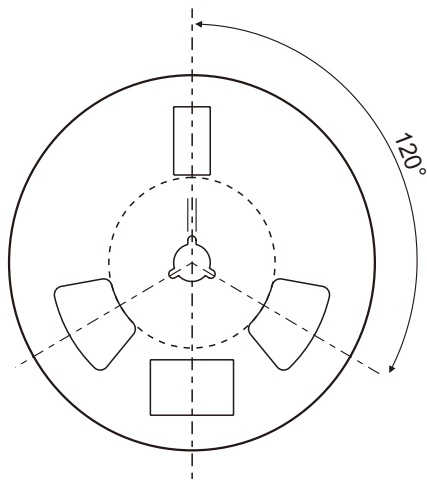
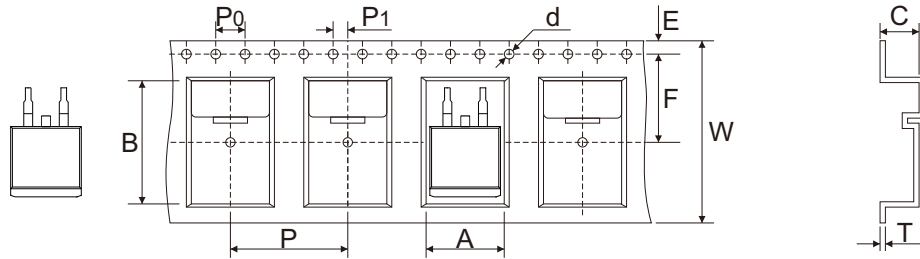


Fig.10 - Gate-Charge Characteristics



Reel Taping Specification

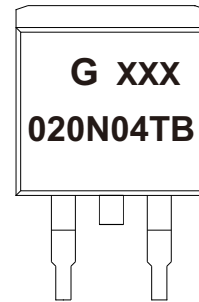


TO-263	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	10.80 ± 0.10	16.13 ± 0.10	5.21 ± 0.10	1.55 ± 0.05	330 ± 0.20	100 ± 0.20	13.00 ± 0.20
	(inch)	0.425 ± 0.004	0.635 ± 0.004	0.205 ± 0.004	0.061 ± 0.002	12.992 ± 0.008	3.937 ± 0.008	0.512 ± 0.008

TO-263	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	11.50 ± 0.10	16.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.35 ± 0.03	24.00 + 0.30 - 0.10	24.00 ± 0.20
	(inch)	0.069 ± 0.004	0.453 ± 0.004	0.630 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.014 ± 0.001	0.945 + 0.012 - 0.004	0.945 ± 0.008

## Marking Code

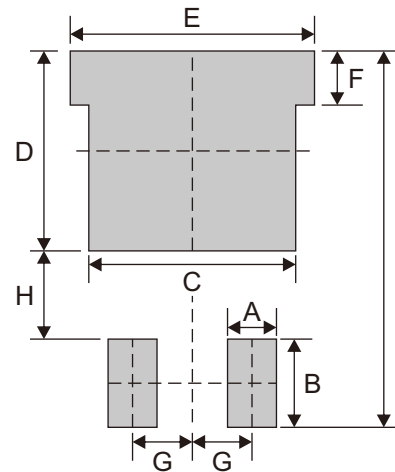
Part Number	Marking Code
ACMS100N04D2-HF	020N04TB



XXX = Control code

## Suggested P.C.B. PAD Layout

SIZE	TO-263	
	(mm)	(inch)
A	2.08	0.110
B	3.50	0.138
C	8.80	0.346
D	9.00	0.354
E	10.4	0.409
F	2.30	0.091
G	2.54	0.100
H	4.00	0.157
I	16.5	0.650



## Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
TO-263	800	13